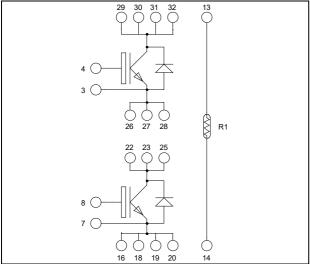


Phase leg Trench + Field Stop IGBT3 Power Module

 $V_{CES} = 1200V$ $I_C = 100A$ @ Tc = 100°C



Pins 29/30/31/32 must be shorted together
Pins 26/27/28/22/23/25 must be shorted together
to achieve a phase leg
Pins 16/18/19/20 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- AlN substrate for improved thermal performance

Benefits

- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

Tibsolate maximum ratings (ref 10b1)							
Symbol	Parameter		Max ratings	Unit			
V_{CES}	Collector - Emitter Voltage		1200	V			
Ţ	Continuous Collector Current	$T_C = 25$ °C	140				
$I_{\rm C}$	Continuous Collector Current	$T_C = 100$ °C	100	A			
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	200				
V_{GE}	Gate – Emitter Voltage		±20	V			
P_{D}	Power Dissipation	$T_C = 25$ °C	595	W			
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	200A @ 1100V				

**CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics (P	Per IGBT)
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Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$ \begin{array}{c c} V_{GE} = 15V & T_j = 25^{\circ}C \\ I_C = 100A & T_j = 125^{\circ}C \\ \end{array} $	$T_j = 25$ °C	1.4	1.7	2.1	V
V CE(sat)	Conector Enfitter Saturation Voltage		$T_j = 125$ °C		2.0		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				400	nA

Dynamic Characteristics (Per IGBT)

·	Characteristic	Test Condition	ıs	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			7200		
C_{oes}	Output Capacitance	$V_{CE} = 25V$			400		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz	f = 1MHz		300		
Q_{G}	Gate charge	$V_{GE} = \pm 15V ; V_{C} = 100A$	$V_{\rm CE}=600{ m V}$		0.9		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Swit	ching (25°C)		260		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			30		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 100A$			420		
T_{f}	Fall Time	$R_G = 3.9\Omega$			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Swit	ching (125°C)		290		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			50		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600\text{V}$ $I_{\text{C}} = 100\text{A}$			520		
T_{f}	Fall Time	$R_G = 3.9\Omega$			90		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		10		mJ
E _{off}	Turn off Energy	$I_C = 100A$ $R_G = 3.9\Omega$	$T_j = 125$ °C		10		Ш
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{E} t_{p} \le 10 \mu s ; T_{j} =$			400		A
R_{thJC}	Junction to Case Thermal Resistance					0.21	°C/W

Reverse diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					1200	V
I_{RM}	Reverse Leakage Current	$V_{R}=1200V$				350	μA
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		100		A
V	Diada Famyand Valtaga	$I_F = 100A$	$T_j = 25$ °C		1.6	2.1	V
V_{F}	Diode Forward Voltage	$V_{GE} = 0V$	$T_j = 125$ °C		1.6		V
+	Reverse Recovery Time		$T_j = 25$ °C		170		ns
ι _{rr}		$T_j = 125$ °C		280		115	
0	Parama Pagarami Changa	$I_F = 100A$ $V_R = 600V$	$T_j = 25$ °C		11		
Qп		$T_j = 125$ °C		20		μС	
E	Davarsa Dagayary Engray	<u> </u>	$T_j = 25$ °C		4.4		mJ
$E_{\rm r}$	Reverse Recovery Energy	ery energy			8.2		1113
R_{thJC}	Junction to Case Thermal Resistance	_				0.32	°C/W



Thermal and package characteristics

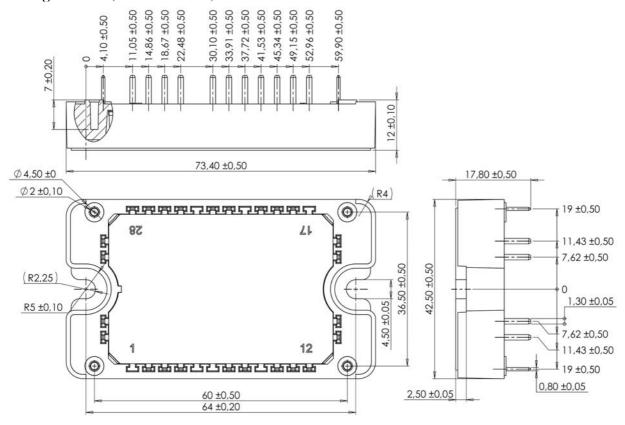
Symbol	l Characteristic				Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000		V
$T_{\rm J}$	Operating junction temperature range			-40	150	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C	25°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T _C =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \begin{array}{l} \text{T: Thermistor temperature} \\ R_T: \text{ Thermistor value at T} \end{array}$$

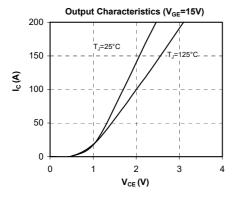
Package outline (dimensions in mm)

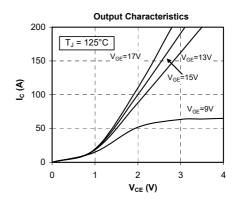


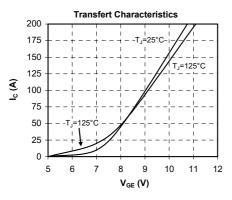
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

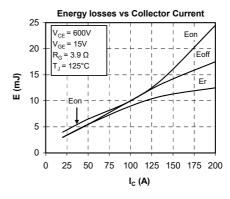


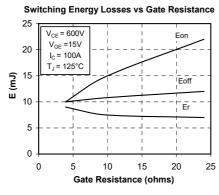
Typical Performance Curve

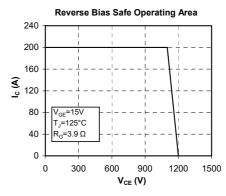


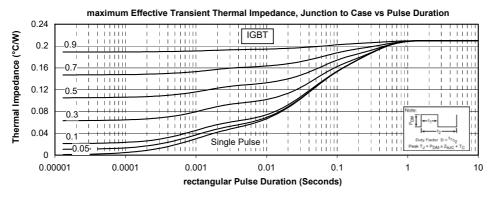




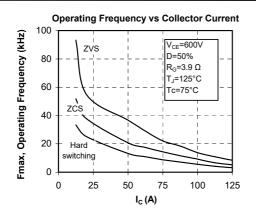


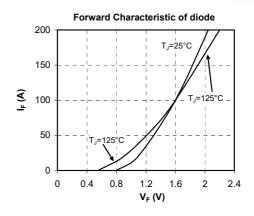


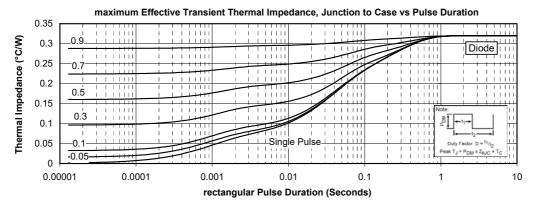














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